

HSB276AS

Silicon Schottky Barrier Diode for Balanced Mixer

HITACHI

ADE-208-838(Z)
Rev. 0
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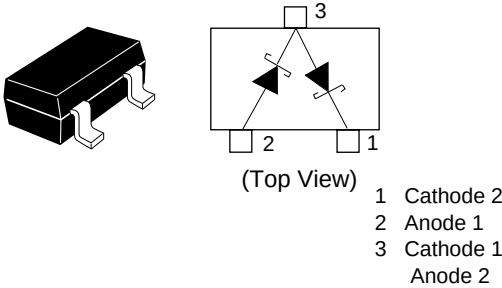
Features

- High forward current, Low capacitance.
- HSB276AS which is interconnected in series configuration is designed for balanced mixer use.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSB276AS	E8	CMPAK

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	5	V
Reverse voltage	V_R	3	V
Average rectified current	I_O^{*1}	30	mA
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

Note 1. Per one device

Electrical Characteristics (Ta = 25°C) *2

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	3	—	—	V	$I_R = 1\text{ mA}$
Reverse current	I_R	—	—	50	μA	$V_R = 0.5\text{ V}$
Forward current	I_F	35	—	—	mA	$V_F = 0.5\text{ V}$
Capacitance	C	—	—	0.90	pF	$V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$
Capacitance deviation	ΔC	—	—	0.10	pF	$V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$
ESD-Capability*1	—	30	—	—	V	$C = 200\text{ pF}$, $R = 0\Omega$

Both forward and reverse direction 1 pulse.

Note 1. Failure criterion ; $I_R \geq 100\mu\text{A}$ at $V_R = 0.5\text{ V}$

Note 2. Per one device

Main Characteristic

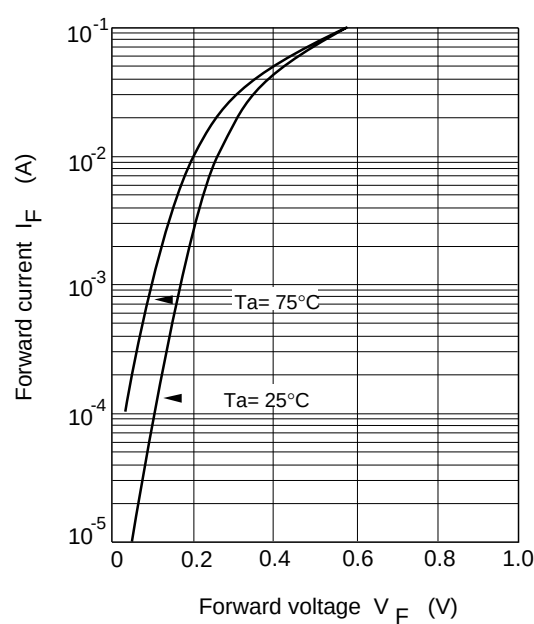


Fig.1 Forward current Vs. Forward voltage

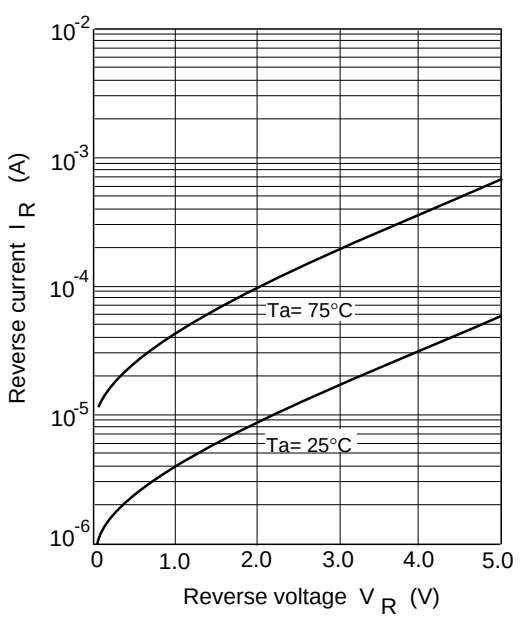


Fig.2 Reverse current Vs. Reverse voltage

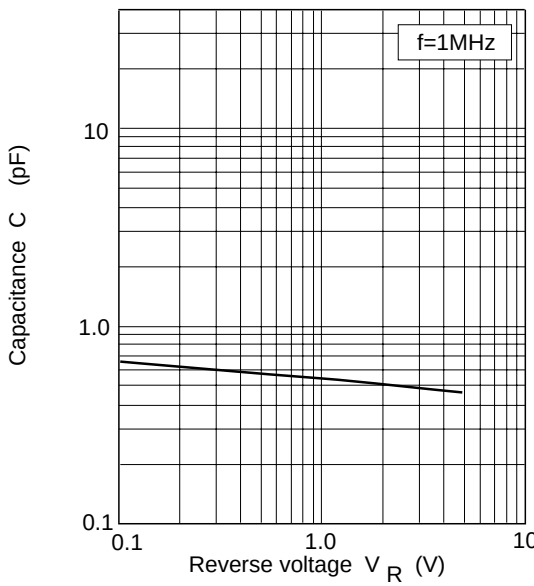


Fig.3 Capacitance Vs. Reverse voltage

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
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Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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